Product data sheet

1. General description

High voltage, high speed planar passivated NPN power switching transistor in a SOT428 (DPAK) surface mountable plastic package.

2. Features and benefits

- Fast switching
- · Low thermal resistance
- · Surface mountable package
- · Very high voltage capability
- · Very low switching and conduction losses

3. Applications

- DC-to-DC converters
- · High frequency electronic lighting ballasts
- Inverters
- Motor control systems

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I _{CM}	peak collector current	Fig. 1; Fig. 2; Fig. 3	-	-	10	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; <u>Fig. 4</u>	-	-	80	W
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	-	1000	V
Static characte	eristics					
h _{FE}	DC current gain	$I_C = 5 \text{ mA}$; $V_{CE} = 5 \text{ V}$; $T_{mb} = 25 ^{\circ}\text{C}$; Fig. 11	10	22	30	
		I_C = 500 mA; V_{CE} = 5 V; T_{mb} = 25 °C; Fig. 11	14	25	35	

NPN power transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base		C
2	С	collector[1]	(7 B S)	В
3	E	emitter		
mb	С	mounting base; connected to collector		E sym123
			DPAK (SOT428)	

[1] it is not possible to make a connection to pin 2 of the SOT428 (DPAK) package.

6. Ordering information

Table 3. Ordering information

Type number	Package						
	Name	Description	Version				
BUJ303AD	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428				

NPN power transistor

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CESM}	collector-emitter peak voltage	V _{BE} = 0 V	-	1000	V
V_{CEO}	collector-emitter voltage	I _B = 0 A	-	500	V
I _C	collector current	Fig. 1; Fig. 2; Fig. 3	-	5	Α
I _{CM}	peak collector current		-	10	Α
I_{B}	base current		-	2	Α
I _{BM}	peak base current		-	4	Α
P _{tot}	total power dissipation	T _{mb} ≤ 25 °C; <u>Fig. 4</u>	-	80	W
T_{stg}	storage temperature		-65	150	°C
T _j	junction temperature		-	150	°C

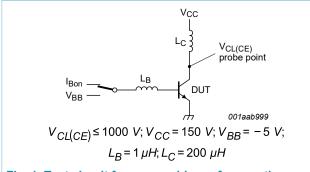


Fig. 1. Test circuit for reverse bias safe operating area

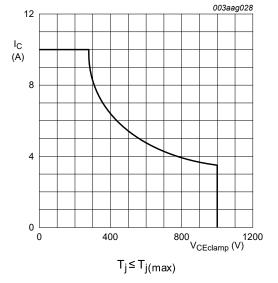
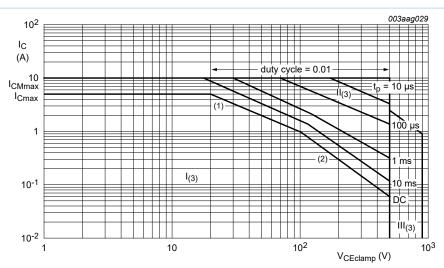


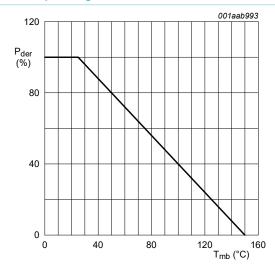
Fig. 2. Reverse bias safe operating area

NPN power transistor



- (1) P_{tot} maximum and P_{tot} peak maximum lines.
- (2) Second breakdown limits.
- (3) I = Region of permissible DC operation.
- II = Extension for repetitive pulse operation.
- III = Extension during turn-on in single transistor converters provided that $R_{BE} \le 100~\Omega$ and $t_p \le 0.6~\mu s$.

Fig. 3. Forward bias safe operating area for Tmb ≤ 25 °C



$$P_{der} = \frac{P_{tot}}{P_{tot}(25^{\circ}C)} \times 100\%$$

Fig. 4. Normalized total power dissipation as a function of mounting base temperature

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NPN power transistor

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	1.56	K/W
R _{th(j-a)}	thermal resistance from junction to ambient free air	printed circuit board (FR4) mounted; minimum footprint	-	75	-	K/W

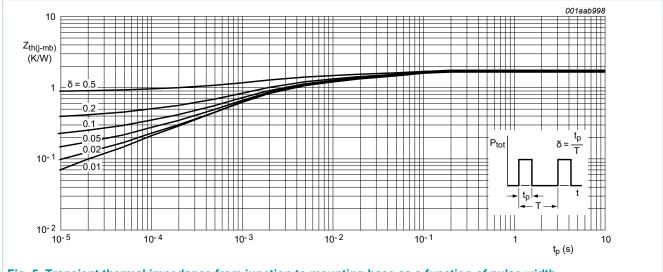


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse width

5 / 13

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Static chara	acteristics						
020	collector-emitter cut-off	V _{BE} = 0 V; V _{CE} = 1000 V	[1]	-	-	1	mA
	current (base shorted)	V _{BE} = 0 V; V _{CE} = 1000 V; T _j = 125 °C	[1]	-	-	2	mA
I _{CBO}	collector-base cut-off current (emitter open)	V _{CB} = 1000 V; I _E = 0 A; T _{mb} = 25 °C	[1]	-	-	1	mA
I _{CEO}	collector-emitter cut-off current (base open)	$V_{CE} = 500 \text{ V}; I_B = 0 \text{ A}; T_{mb} = 25 \text{ °C}$	[1]	-	-	0.1	mA
I _{EBO}	emitter-base cut-off current (collector open)	$V_{EB} = 9 \text{ V; } I_{C} = 0 \text{ A; } T_{mb} = 25 ^{\circ}\text{C}$		-	-	0.1	mA
V_{CEOsus}	collector-emitter sustaining voltage (base open)	$I_B = 0 \text{ A}; I_C = 100 \text{ mA}; L_C = 25 \text{ mH};$ $T_{mb} = 25 \text{ °C}; \underline{\text{Fig. 6}}; \underline{\text{Fig. 7}}$		500	-	-	V
V_{CEsat}	collector-emitter saturation voltage	$I_C = 3 \text{ A}; I_B = 0.6 \text{ A}; T_{mb} = 25 \text{ °C}; Fig. 8; Fig. 9}$		-	0.25	1.5	V
V_{BEsat}	base-emitter saturation voltage	$I_C = 3 \text{ A}; I_B = 0.6 \text{ A}; T_{mb} = 25 \text{ °C};$ Fig. 10		-	0.97	1.3	V
h _{FE}	DC current gain	$I_C = 5 \text{ mA}$; $V_{CE} = 5 \text{ V}$; $T_{mb} = 25 \text{ °C}$; Fig. 11		10	22	30	
		I_C = 500 mA; V_{CE} = 5 V; T_{mb} = 25 °C; Fig. 11		14	25	35	
h _{FEsat}	DC saturation current gain	$I_C = 2.5 \text{ A}; V_{CE} = 5 \text{ V}; T_{mb} = 25 ^{\circ}\text{C};$ Fig. 11		10	13.5	17	
		I _C = 3 A; V _{CE} = 5 V; T _{mb} = 25 °C; Fig. 11		-	12	-	
Dynamic ch	naracteristics (switching tin	nes - resistive load)					
t _s	storage time	I _C = 2.5 A; I _{Bon} = 0.5 A; I _{Boff} = -0.5 A;		-	3.4	4	μs
t _f	fall time	$R_L = 75 \Omega$; $T_{mb} = 25 °C$; <u>Fig. 12</u> ; <u>Fig. 13</u>		-	0.33	0.45	μs
Dynamic ch	naracteristics (switching tin	nes - inductive load)					
t _s	storage time	I _C = 2.5 A; I _{Bon} = 0.5 A; V _{BB} = -5 V; L _B = 1 μH; T _{mb} = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>		-	1.4	1.6	μs
				-	1.7	1.9	μs
t _f	fall time	$I_C = 2.5 \text{ A}; I_{Bon} = 0.5 \text{ A}; V_{BB} = -5 \text{ V};$ $L_B = 1 \mu\text{H}; T_j = 100 \text{ °C}; Fig. 14; Fig. 15$		-	145	160	ns
				-	160	200	ns
t _f	fall time	I _C = 2.5 A; I _{Bon} = 0.5 A; V _{BB} = -5 V;		-	145	160	

^[1] Measured with half-sine wave voltage (curve tracer).

NPN power transistor

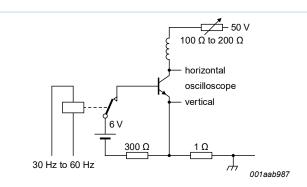


Fig. 6. Test circuit for collector-emitter sustaining voltage

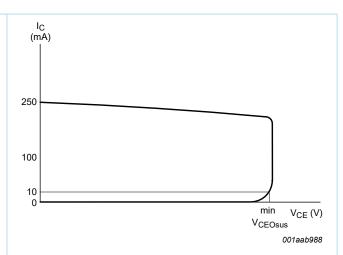


Fig. 7. Oscilloscope display for collector-emitter sustaining voltage test waveform

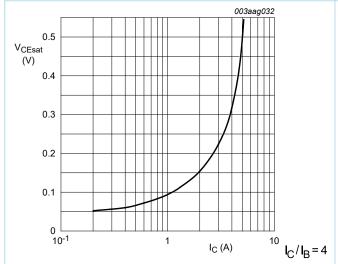


Fig. 8. Collector-emitter saturation voltage as a function of collector current; typical values

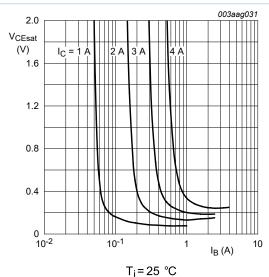


Fig. 9. Collector-emitter saturation voltage as a function of base current; typical values

NPN power transistor

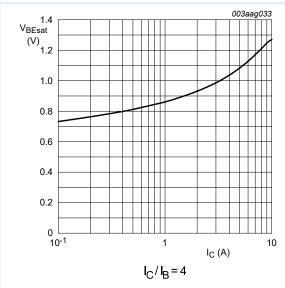


Fig. 10. Base-emitter saturation voltage as a function of collector current; typical values

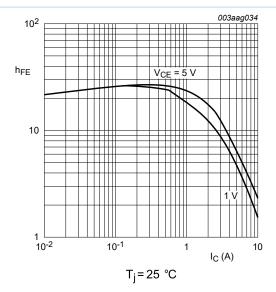
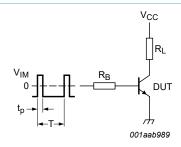


Fig. 11. DC current gain as a function of collector current; typical values



 V_{IM} = -6 to +8 V; V_{CC} = 250 V; t_p = 20 μ s; δ = $\frac{t_p}{T}$ = 0.01 R_B and R_L calculated from I_{Con} and I_{Bon} requirements.

Fig. 12. Test circuit for resistive load switching

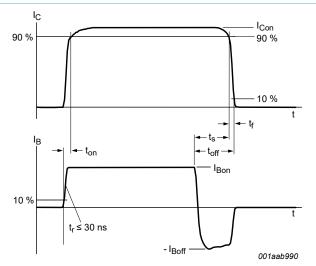
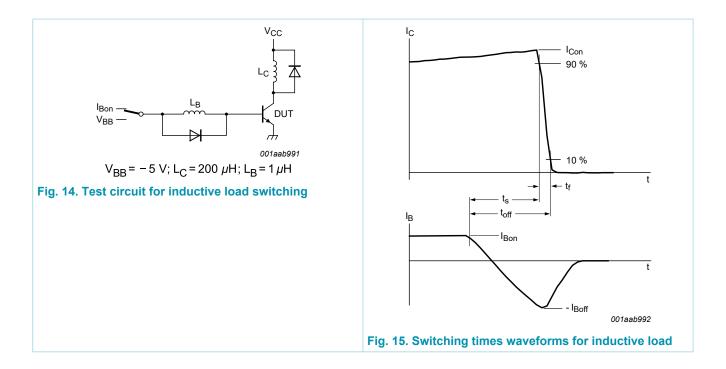


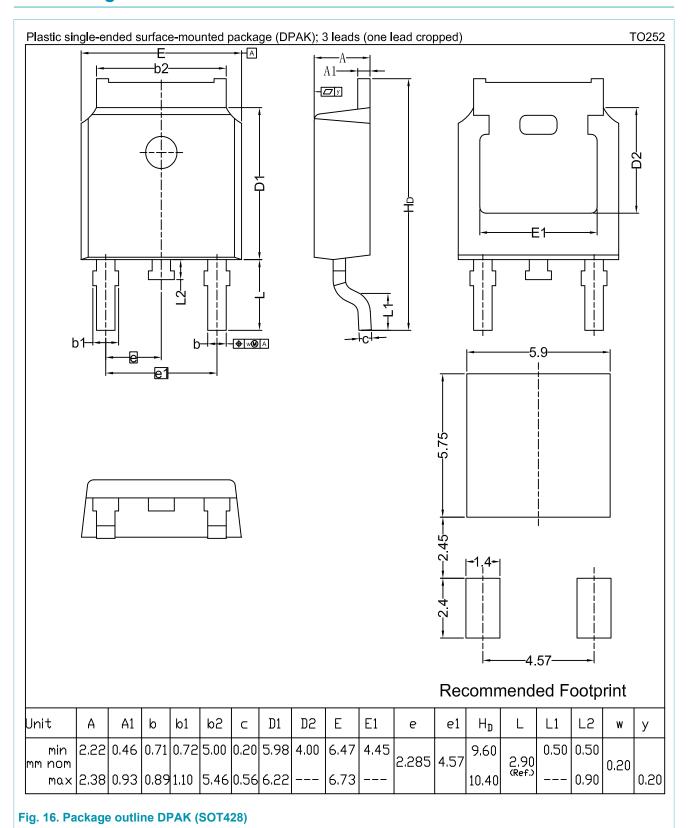
Fig. 13. Switching times waveforms for resistive load

NPN power transistor



9 / 13

10. Package outline



NPN power transistor

11. Legal information

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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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11 / 13

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NPN power transistor

12. Contents

1.	General description	1
2.	Features and benefits	. 1
3.	Applications	. 1
4.	Quick reference data	1
5.	Pinning information	2
6.	Ordering information	2
7.	Limiting values	. 3
8.	Thermal characteristics	. 5
9.	Characteristics	6
10.	Package outline	10
11.	. Legal information	11

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